

Amendments to the Specification

Please amend original paragraph [045] as follows:

As noted above with regard to Figure 3C, the four-mask process includes the diffraction slit mask ~~360~~350. Figure 4 shows one example of a suitable slit mask. As shown in Figure 4, the slit mask includes a U-shaped source forming pattern 401, a '-shaped drain forming pattern 402, and a slit-pattern 403 that acts as a channel pattern formed between the source and drain electrode patterns 401 and 402. The channel pattern shown increases the size of the TFT channel between the source and drain electrodes 306, 307 for enhanced signal characteristics.